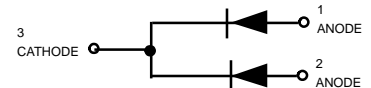
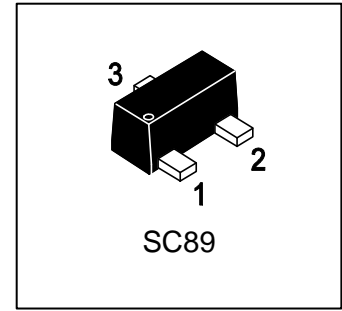


LDAN222T1G

S-LDAN222T1G

Common Cathode Silicon
Dual Switching Diode



1. FEATURES

- Fast Trr
- Low CD
- We declare that the material of product compliance with RoHS requirements and Halogen Free.
- S- prefix for automotive and other applications requiring unique site and control change requirements; AEC-Q101 qualified and PPAP capable.

2. DEVICE MARKING AND RESISTOR VALUES

| Device | Marking | Shipping |
|------------|---------|-----------------|
| LDAN222T1G | N9 | 3000/Tape&Reel |
| LDAN222T3G | N9 | 10000/Tape&Reel |

3. MAXIMUM RATINGS(Ta = 25°C)

| Parameter | Symbol | Limits | Unit |
|------------------------------------|--------|--------|------|
| Reverse Voltage | VR | 100 | V |
| Peak Reverse Voltage | VRM | 100 | V |
| Forward Current | IF | 100 | mA |
| Peak Forward Current | IFM | 300 | mA |
| Peak Forward Surge Current(Note 1) | IFSM | 2 | A |

4. THERMAL CHARACTERISTICS

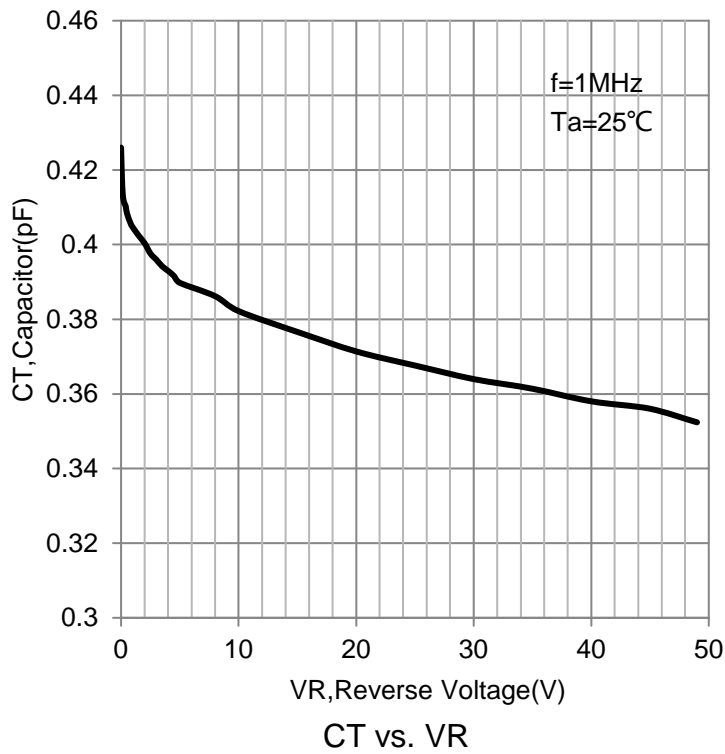
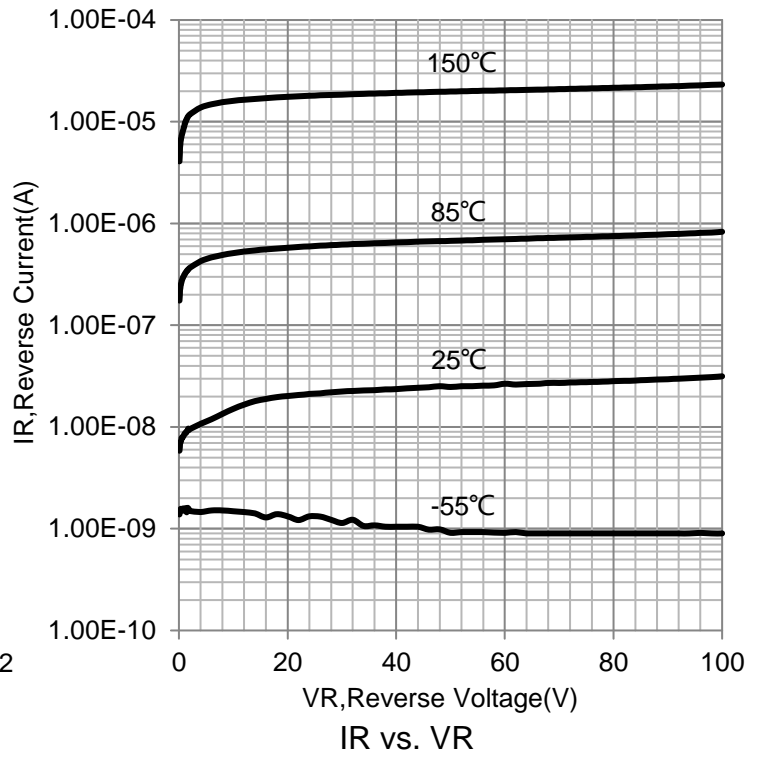
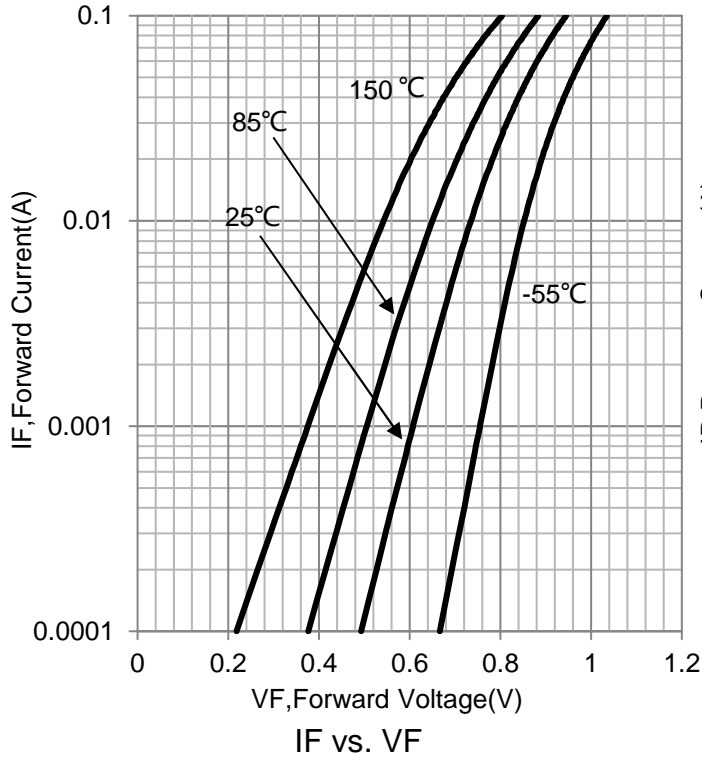
| Parameter | Symbol | Limits | Unit |
|---------------------------|--------|----------|------|
| Power Dissipation | PD | 150 | mW |
| Junction Temperature | Tj | 150 | °C |
| Storage Temperature Range | Tstg | -55~+150 | °C |

1. t = 1 μS

5. ELECTRICAL CHARACTERISTICS (Ta= 25°C)

| Characteristic | Symbol | Min. | Typ. | Max. | Unit |
|--|--------|--------|--------|-----------|------|
| Reverse Voltage Leakage Current (VR = 70 V) (VR = 100 V) | IR | - - | - - | 0.1 10 | μA |
| Forward Voltage (IF = 100 mA) | VF | - | - | 1.2 | V |
| Reverse Breakdown Voltage (IR = 100 μA) | VR | 100 | - | - | V |
| Diode Capacitance (VR = 6.0 V, f = 1.0 MHz) | CD | - | - | 3.5 | pF |
| Reverse Recovery Time (IF = 5.0 mA, VR = 6.0 V, RL = 100 Ω, Irr = 0.1 IR) | Trr | - | - | 4.0 | ns |

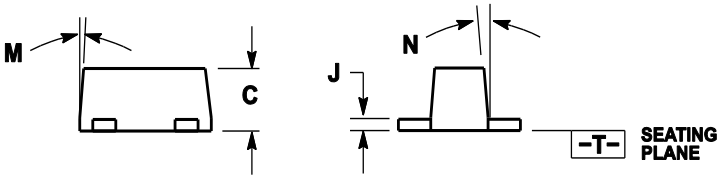
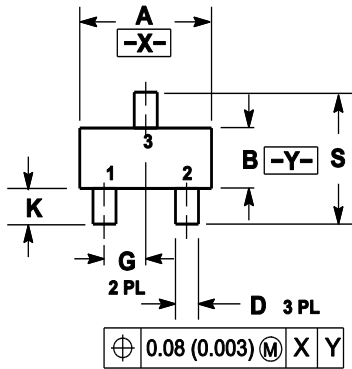
6. ELECTRICAL CHARACTERISTICS CURVES



7. OUTLINE AND DIMENSIONS

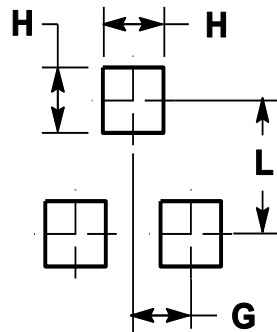
Notes:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.



| DIM | MILLIMETERS | | | INCHES | | |
|-----|-------------|------|------|----------|-------|-------|
| | MIN | NOM | MAX | MIN | NOM | MAX |
| A | 1.50 | 1.60 | 1.70 | 0.059 | 0.063 | 0.067 |
| B | 0.75 | 0.85 | 0.95 | 0.030 | 0.034 | 0.040 |
| C | 0.60 | 0.70 | 0.80 | 0.024 | 0.028 | 0.031 |
| D | 0.23 | 0.28 | 0.33 | 0.009 | 0.011 | 0.013 |
| G | 0.50BSC | | | 0.020BSC | | |
| H | 0.53REF | | | 0.021REF | | |
| J | 0.10 | 0.15 | 0.20 | 0.004 | 0.006 | 0.008 |
| K | 0.30 | 0.40 | 0.50 | 0.012 | 0.016 | 0.02 |
| L | 1.10REF | | | 0.043REF | | |
| M | --- | --- | 10° | --- | --- | 10° |
| N | --- | --- | 10° | --- | --- | 10° |
| S | 1.50 | 1.60 | 1.70 | 0.059 | 0.063 | 0.067 |

8. SOLDERING FOOTPRINT



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